

# N-Channel Enhancement Mode MOSFET

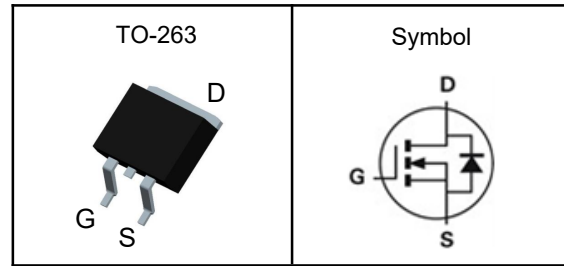
## Features

- Fast switching speed
- Reliable and Rugged
- ROHS Compliant
- 100% UIS and Rg Tested

## Applications

- High Frequency Point-of-Load Synchronous Buck Converter
- Networking DC-DC Power System
- Load Switch

## Pin Description



$V_{DSS}$	60	V
$R_{DS(ON)-Typ}$	2.6	m $\Omega$
$I_D$	150	A

## Absolute Maximum Ratings ( $T_C=25^\circ\text{C}$ , Unless Otherwise Noted)

Symbol	Parameter	N-Channel	Unit
$V_{DSS}$	Drain-Source Voltage	60	V
$V_{GSS}$	Gate-Source Voltage	$\pm 20$	V
$T_J$	Maximum Junction Temperature	-55 to 150	$^\circ\text{C}$
$T_{STG}$	Storage Temperature Range	-55 to 150	$^\circ\text{C}$
$I_{DM}^{①}$	Pulse Drain Current Tested	600	A
$I_D$	Continuous Drain Current	150	A
$P_D$	Maximum Power Dissipation	220	W
$E_{AS}$	Avalanche Energy, Single pulse	465	mJ

## Thermal Characteristics

Symbol	Parameter	Rating	Unit
$R_{\theta JA}$	Thermal Resistance-Junction to Ambient	62	$^\circ\text{C}/\text{W}$
$R_{\theta JC}$	Thermal Resistance-Junction to Case	0.68	$^\circ\text{C}/\text{W}$

Note ① : Max. current is limited by bonding wire.

Note ② : UIS tested and pulse width are limited by maximum junction temperature  $150^\circ\text{C}$ .

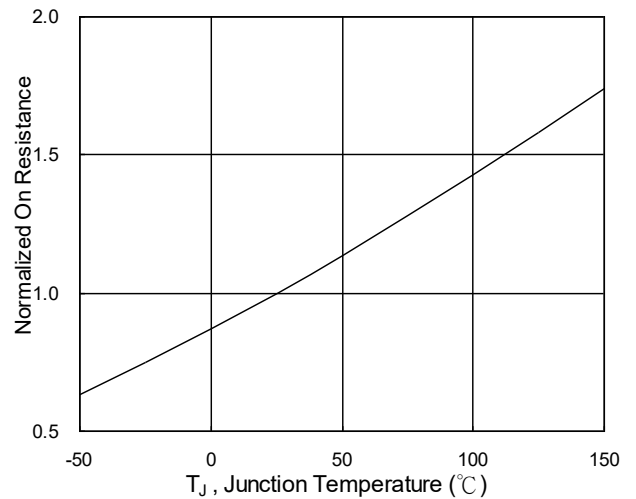
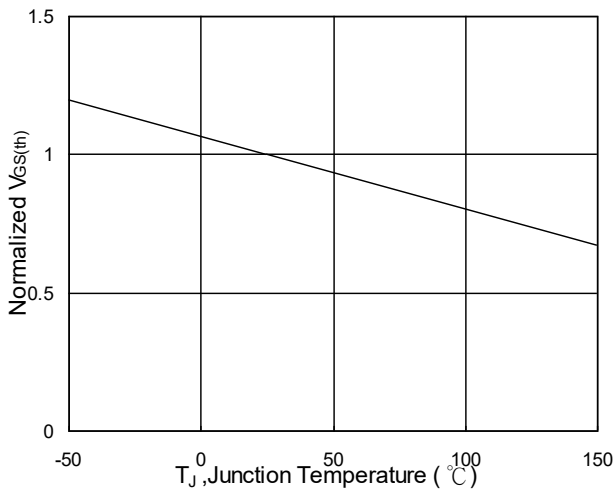
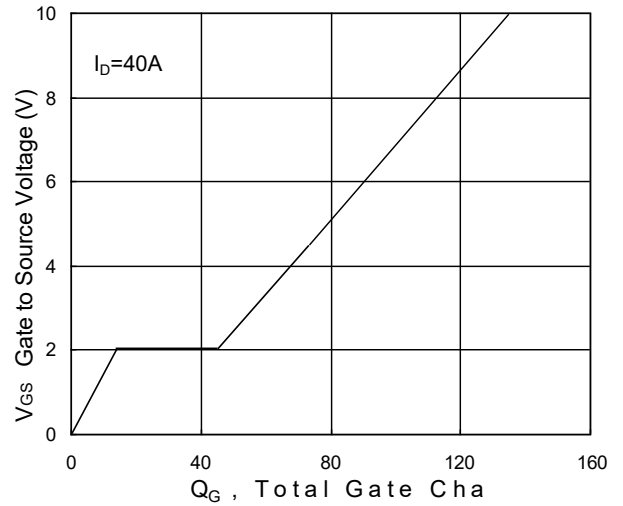
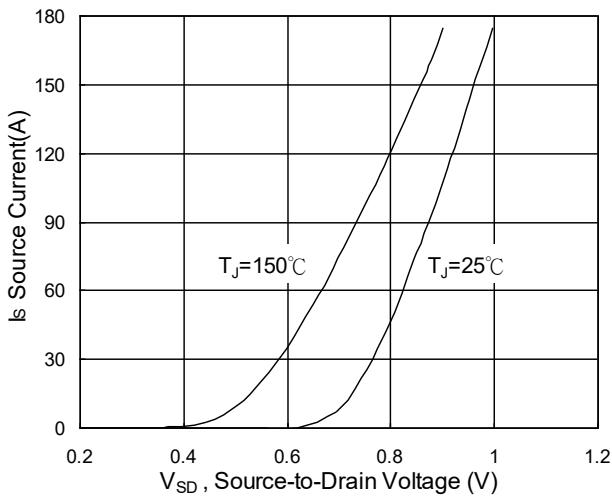
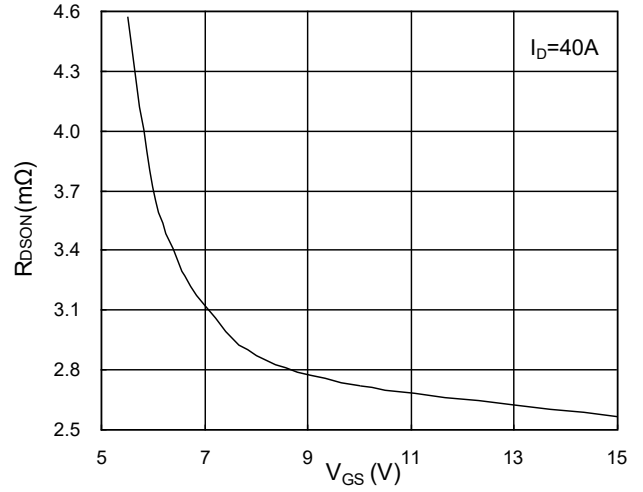
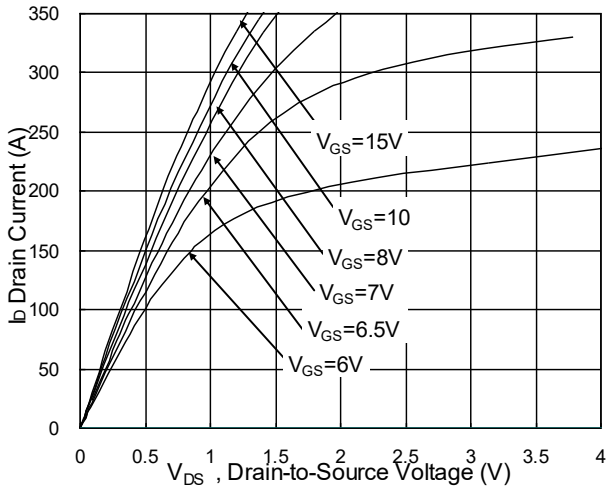
Note ③ : Surface Mounted on  $1\text{in}^2$  FR-4 board with 1oz.

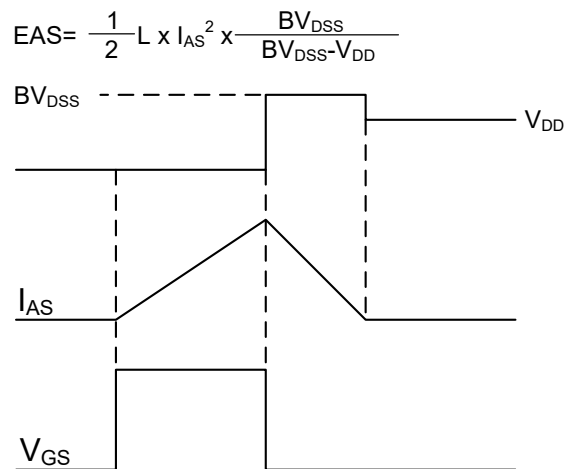
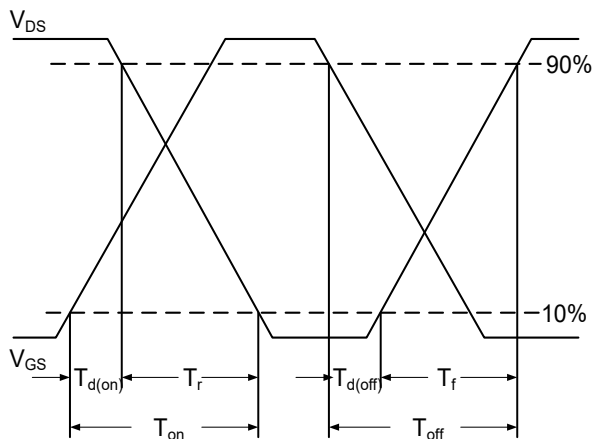
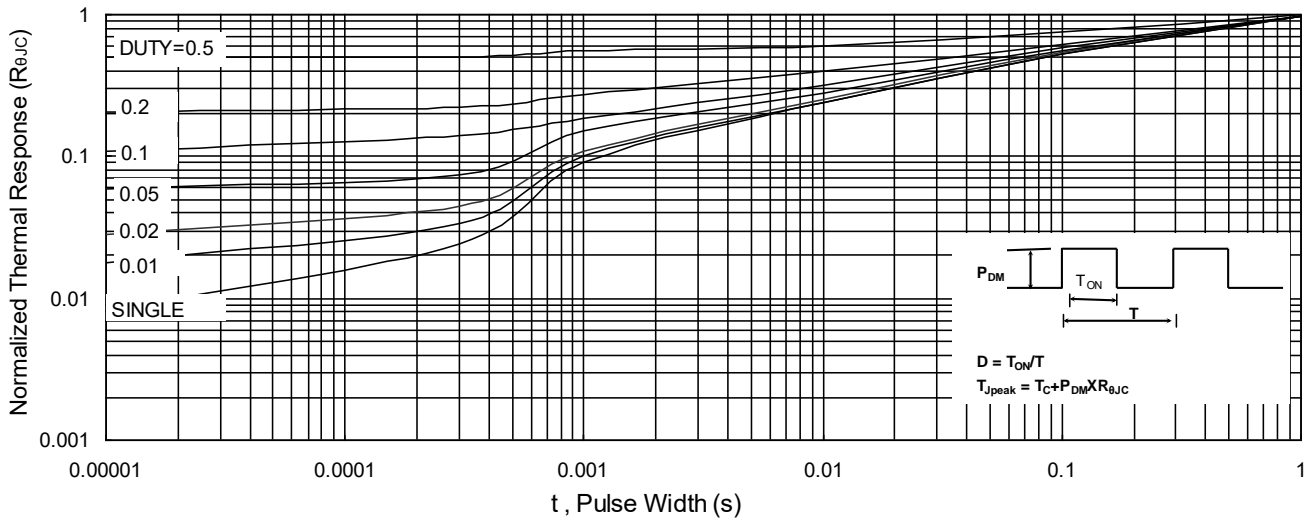
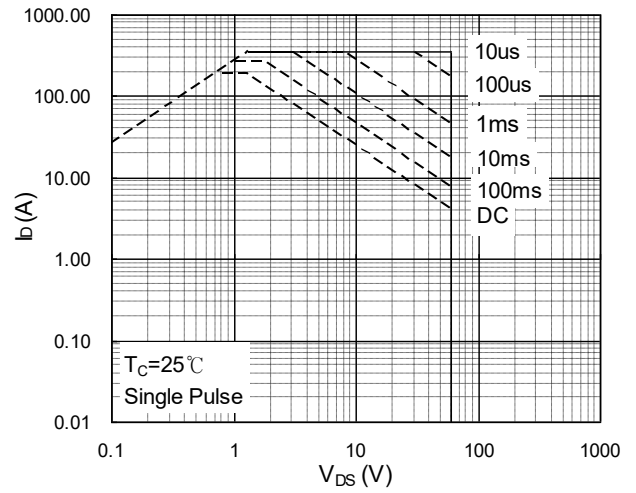
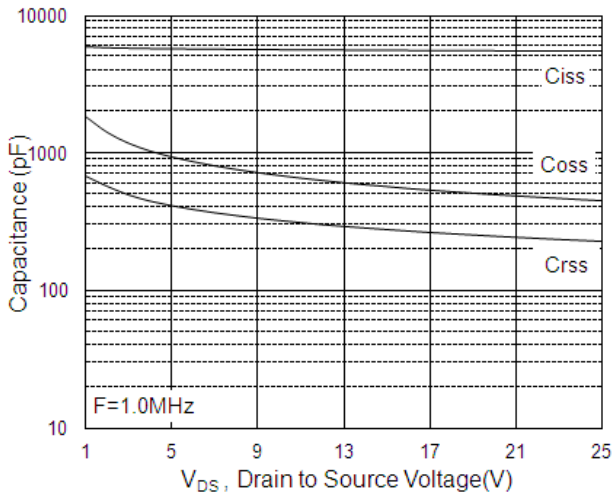
**N-Channel Enhancement Mode MOSFET****Electrical Characteristics** ( $T_J=25^\circ\text{C}$ , Unless Otherwise Noted)

Symbol	Parameter	Test Conditions	Min	Typ	Max	Unit
<b>Static Electrical Characteristics</b>						
$BV_{DSS}$	Drain-Source Breakdown Voltage	$V_{GS}=0V, I_D=250\mu A$	60	---	---	V
$I_{DSS}$	Zero Gate Voltage Drain Current	$V_{DS}=60V, V_{GS}=0V$	---	---	1	$\mu A$
$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS}=V_{GS}, I_D=250\mu A$	2.0	---	4.0	V
$I_{GSS}$	Gate Leakage Current	$V_{GS}=\pm 20V, V_{DS}=0V$	---	---	$\pm 100$	nA
$R_{DS(on)}$	Drain-Source On-state Resistance	$V_{GS}=10V, I_D=40A$	---	2.6	3.4	$m\Omega$
		$V_{GS}=4.5V, I_D=20A$	---	3.5	4.2	$m\Omega$
<b>Dynamic Characteristics</b> <sup>⑤</sup>						
$C_{iss}$	Input Capacitance	$V_{GS}=0V, V_{DS}=30V, \text{Freq.}=1\text{MHz}$	---	5800	---	pF
$C_{oss}$	Output Capacitance		---	930	---	
$C_{rss}$	Reverse Transfer Capacitance		---	412	---	
$T_{d(on)}$	Turn-on Delay Time	$V_{DD}=30V, V_{GS}=10V, R_G=2.7\Omega, I_D=40A$	---	21	---	nS
$T_r$	Turn-on Rise Time		---	95	---	
$T_{d(off)}$	Turn-off Delay Time		---	65	---	
$T_f$	Turn-off Fall Time		---	84	---	
$Q_g$	Total Gate Charge	$V_{GS}=10V, V_{DS}=30V, I_D=40A$	---	136	---	nC
$Q_{gs}$	Gate-Source Charge		---	30	---	
$Q_{gd}$	Gate-Drain Charge		---	57	---	
<b>Source-Drain Characteristics</b>						
$V_{SD}$ <sup>④</sup>	Diode Forward Voltage	$I_S=40A, V_{GS}=0V$	---	---	1.2	V
$t_{rr}$	Reverse Recovery Time	$I_F=40A, di_F/dt=100A/\mu s$	---	55	---	nS
$Q_{rr}$	Reverse Recovery Charge		---	84	---	nC

Note ④: Pulse test (pulse width $\leq 300\mu s$ , duty cycle $\leq 2\%$ ).

Note ⑤: Guaranteed by design, not subject to production testing.

**N-Channel Enhancement Mode MOSFET**
**Typical Characteristics**


**N-Channel Enhancement Mode MOSFET**


$$EAS = \frac{1}{2} L \times I_{AS}^2 \times \frac{BV_{DSS}}{BV_{DSS} - V_{DD}}$$

**N-Channel Enhancement Mode MOSFET**
**TO-263 Package Outline Data**
